

HAT1069C

Silicon P Channel Power MOS FET Power Switching

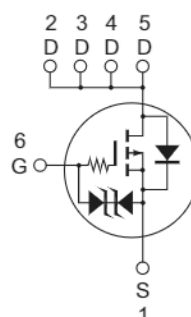
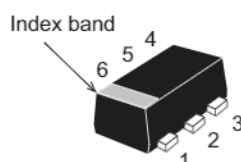
R07DS1169EJ0400
(Previous: REJ03G0164-0300)
Rev.4.00
Mar 19, 2014

Features

- Low on-resistance
 $R_{DS(on)} = 38 \text{ m}\Omega$ typ (at $V_{GS} = -4.5 \text{ V}$)
- High speed switching
- Capable of 1.8 V gate drive
- High density mounting

Outline

RENESAS Package code: PWSF0006JA-A
(Package name: CMFPAK-6)



1. Source
2. Drain
3. Drain
4. Drain
5. Drain
6. Gate

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	-12	V
Gate to source voltage	V_{GS}	± 8	V
Drain current	I_D	-4	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-16	A
Body-drain diode reverse drain current	I_{DR}	-4	A
Channel dissipation	P_{ch} ^{Note2}	900	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes: 1. $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$

2. When using the glass epoxy board. (FR4 40 × 40 × 1.6 mm)

Electrical Characteristics

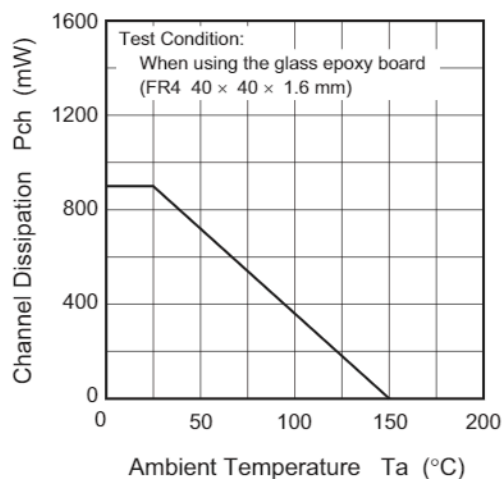
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-12	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 8	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 6.4 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -12 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.3	—	-1.2	V	$V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	38	52	$\text{m}\Omega$	$I_D = -1.5 \text{ A}$, $V_{GS} = -4.5 \text{ V}$
	$R_{DS(on)}$	—	48	70	$\text{m}\Omega$	$I_D = -1.5 \text{ A}$, $V_{GS} = -2.5 \text{ V}$
	$R_{DS(on)}$	—	60	93	$\text{m}\Omega$	$I_D = -1.5 \text{ A}$, $V_{GS} = -1.8 \text{ V}$
Forward transfer admittance	$ y_{fs} $	5	8	—	S	$I_D = -1.5 \text{ A}$, $V_{DS} = -10 \text{ V}$
Input capacitance	C_{iss}	—	1380	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	C_{oss}	—	235	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	115	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	16	—	nC	$V_{DS} = -10 \text{ V}$
Gate to source charge	Q_{gs}	—	3	—	nC	$V_{GS} = -4.5 \text{ V}$
Gate to drain charge	Q_{gd}	—	6.2	—	nC	$I_D = -3 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	35	—	ns	$V_{GS} = -4 \text{ V}$, $I_D = -1.5 \text{ A}$
Rise time	t_r	—	150	—	ns	$V_{DD} \cong -10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	490	—	ns	$R_L = 6.6 \text{ }\Omega$
Fall time	t_f	—	350	—	ns	$R_g = 4.7 \text{ }\Omega$
Body-drain diode forward voltage	V_{DF}	—	-0.8	-1.1	V	$I_F = -4 \text{ A}$, $V_{GS} = 0$ ^{Note3}

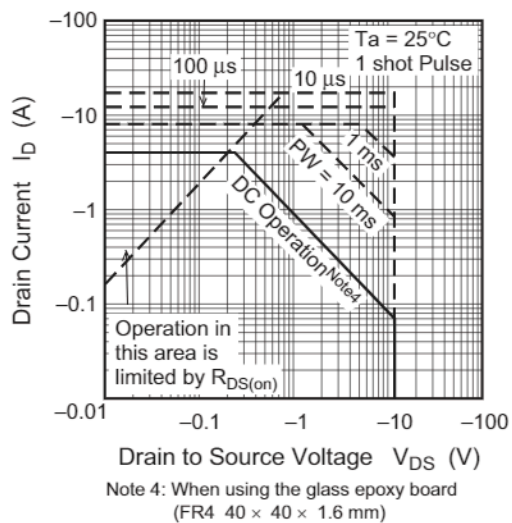
Notes: 3. Pulse test

Main Characteristics

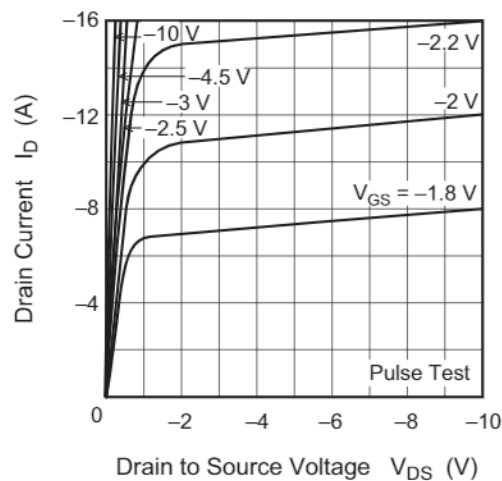
Power vs. Temperature Derating



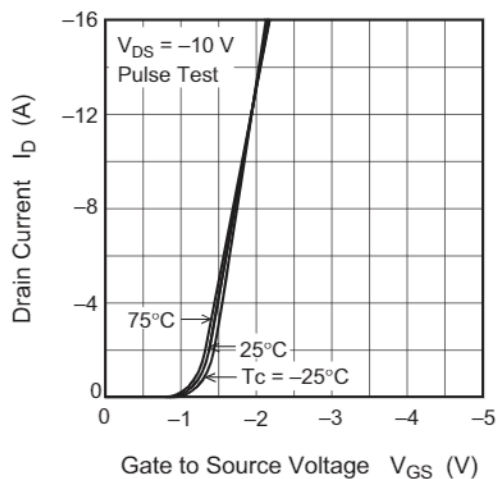
Maximum Safe Operation Area



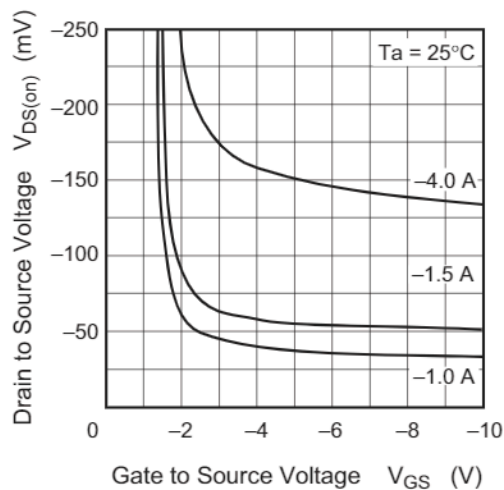
Typical Output Characteristics



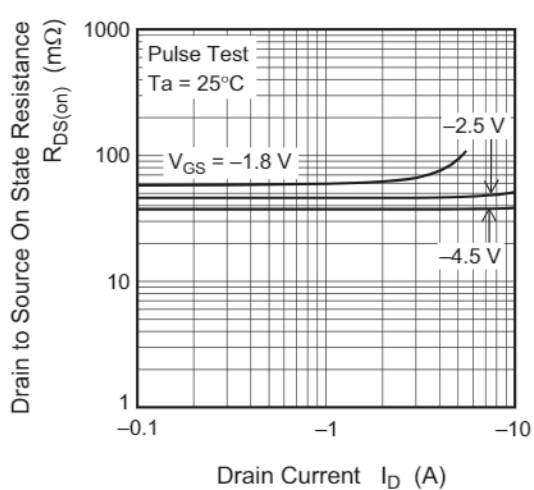
Typical Transfer Characteristics



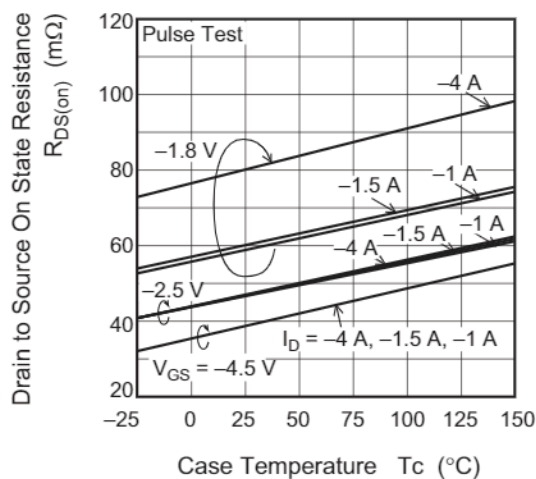
Drain to Source Saturation Voltage vs. Gate to Source Voltage



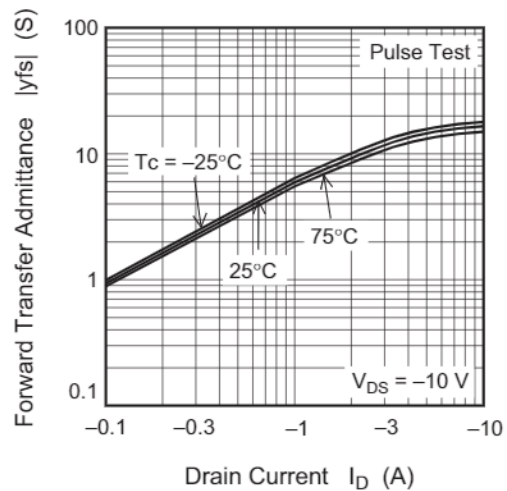
Static Drain to Source on State Resistance vs. Drain Current



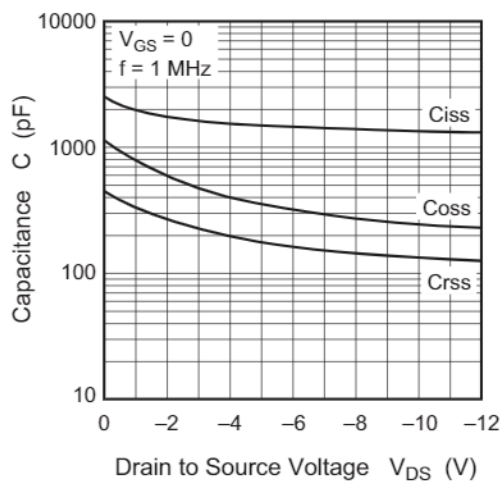
Static Drain to Source on State Resistance vs. Temperature



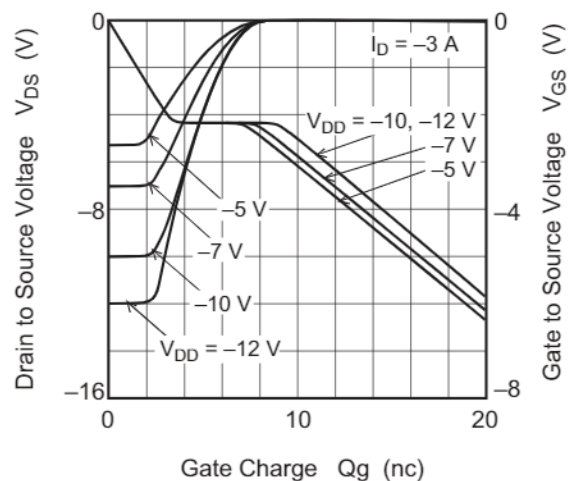
Forward Transfer Admittance vs. Drain Current



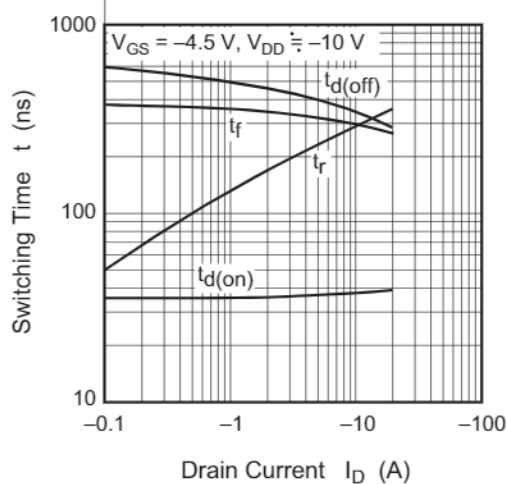
Typical Capacitance vs. Drain to Source Voltage



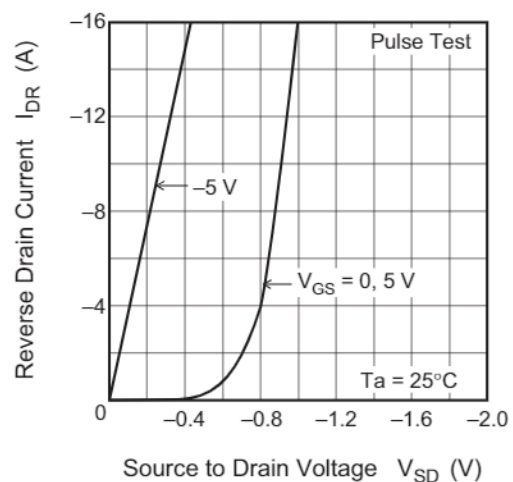
Dynamic Input Characteristics



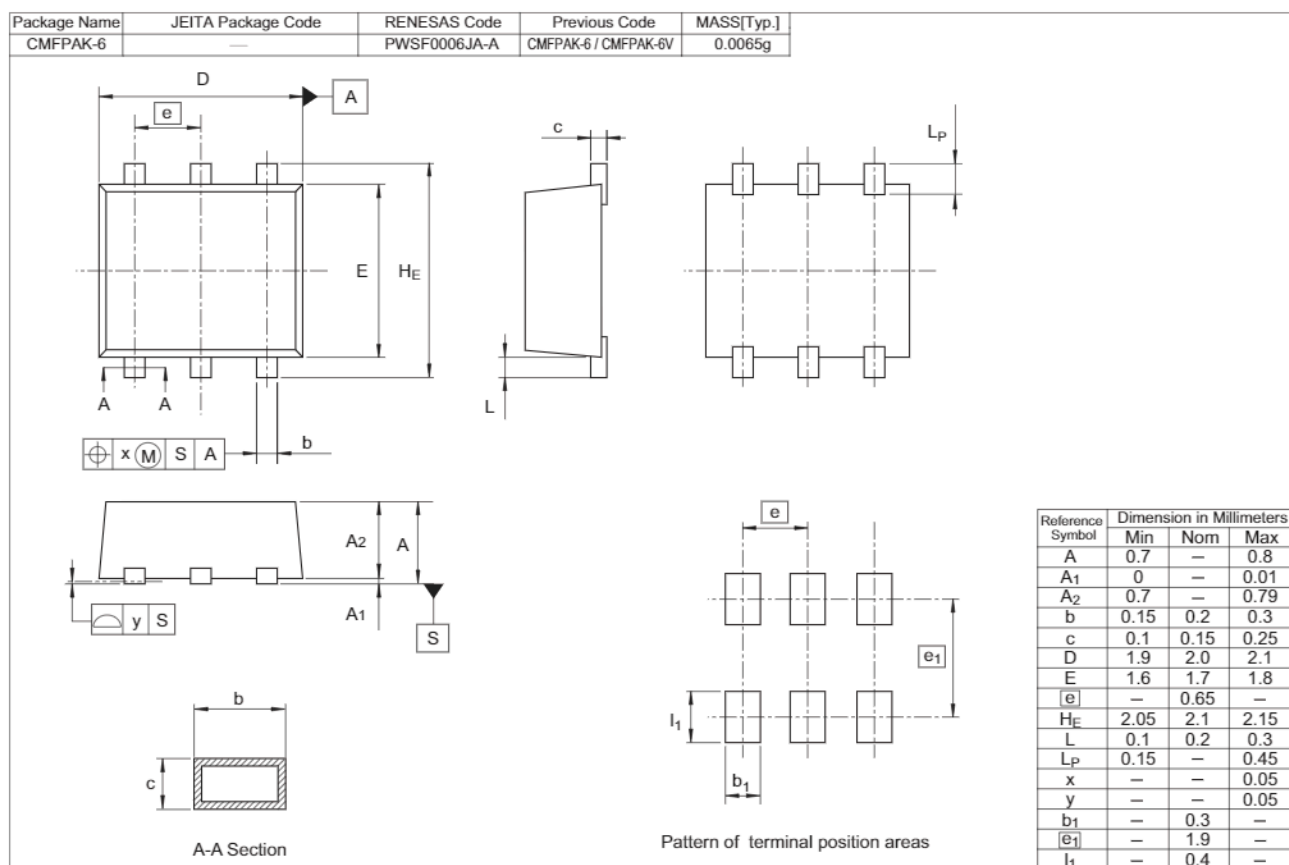
Switching Characteristics



Reverse Drain Current vs. Source to Drain Voltage



Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
HAT1069C-EL-E	3000 pcs	Taping

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Renesas Electronics America Inc.
2801 Scott Boulevard Santa Clara, CA 95050-2549, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852-2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
12F., 234 Teheran-ro, Gangnam-gu, Seoul, 135-920, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141